

## **Supporting Information**

### Effect of long chain fatty acid on the memory switching behavior of tetraindolyl derivative

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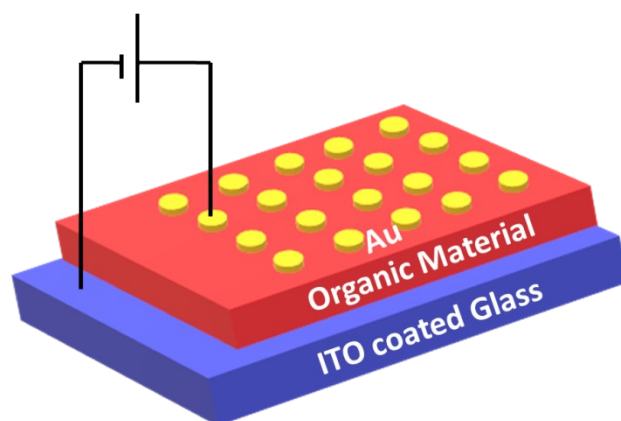
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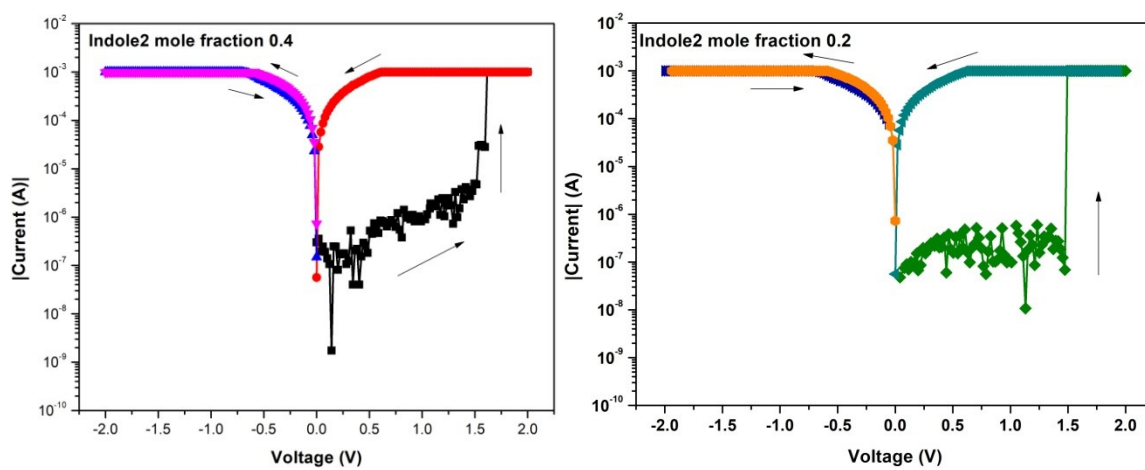
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**Figure S8:** FESEM image of bare ITO.

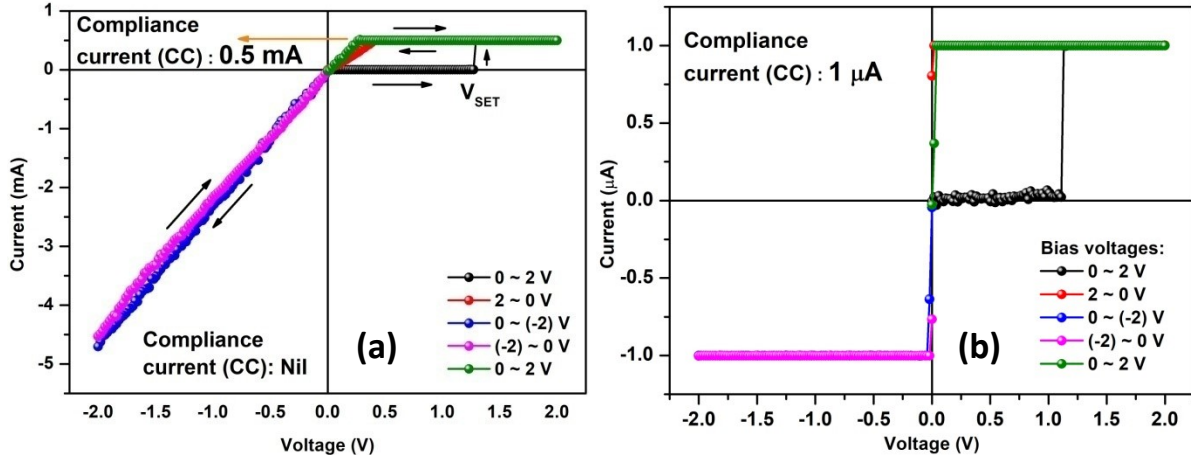
**Figure. S9:** Variation of SET voltages ( $V_{Th}$ ) with the active layer thickness of the devices.



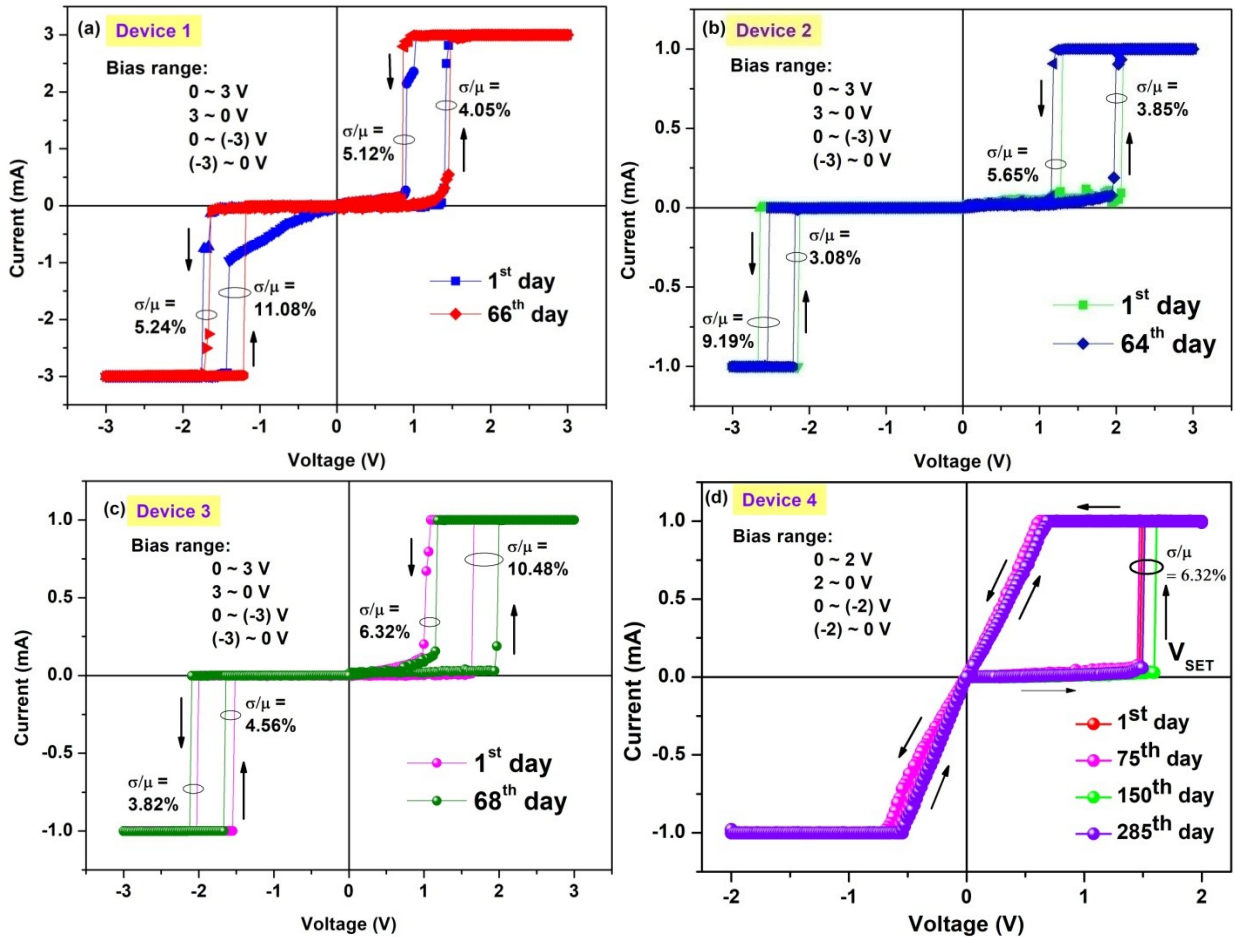
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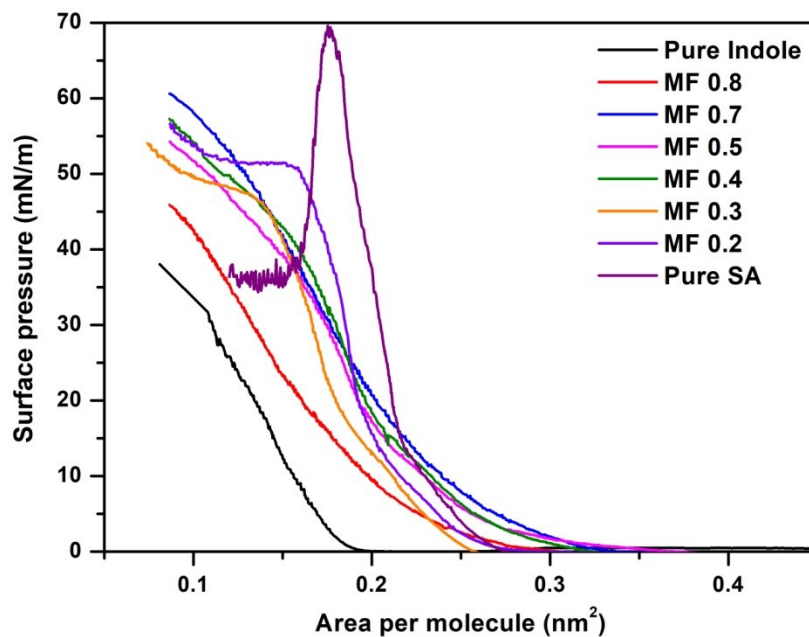
**Figure S2:** I-V curves corresponding to the Indole2 mole fraction 0.4 and 0.2.



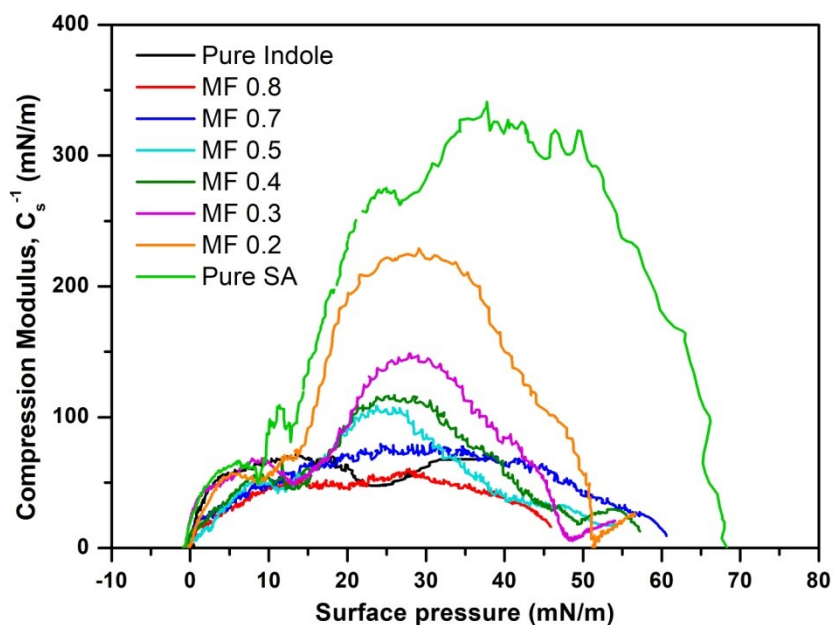
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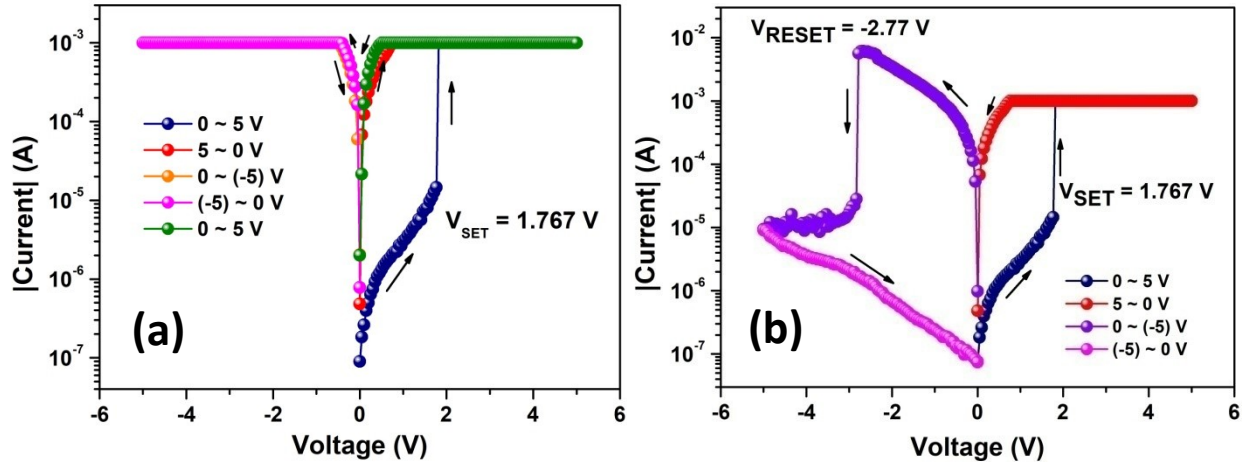
**Figure S4:** I-V characteristics of the devices to get the idea of stability of the device during the period of 66 days (Device 1), 64 days (Device 2), 68 days (Device 3) and 285 days (Device 4).



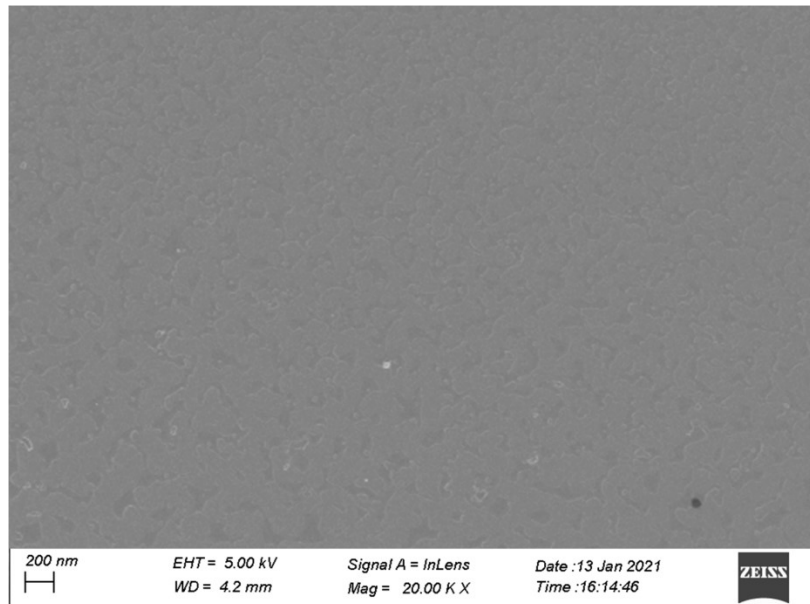
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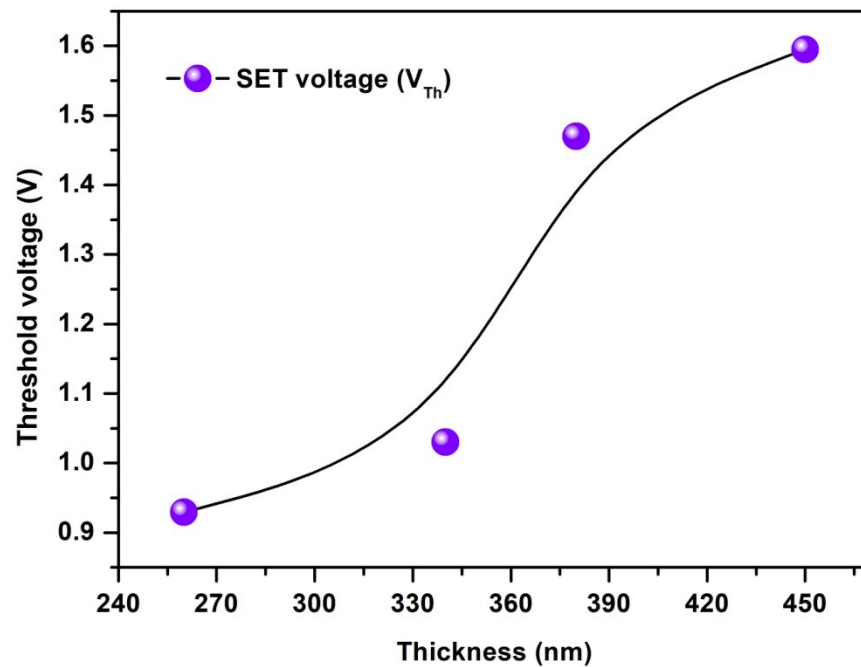
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